TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SD1220

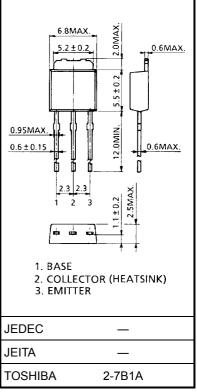
Power Amplifier Applications

Complementary to 2SB905

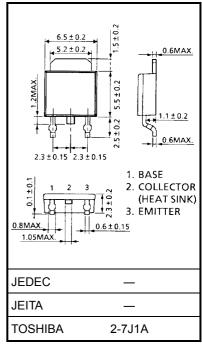
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V_{CBO}	150	V	
Collector-emitter voltage		V _{CEO}	150	V	
Emitter-base voltage		V _{EBO}	6	V	
Collector current		I _C	1.5	А	
Base current		Ι _Β	1.0	А	
Collector power dissipation	Ta = 25°C	PC	1.0	W	
	Tc = 25°C	FC	10		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	−55 to 150	°C	

Unit: mm



Weight: 0.36 g (typ.)



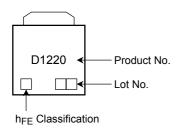
Weight: 0.36 g (typ.)

Electrical Characteristics (Ta = 25°C)

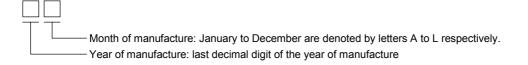
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 150 V, I _E = 0	_	_	1.0	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 6 V, I _C = 0	-	-	1.0	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	150	_	_	٧
DC current gain	h _{FE} (Note)	V _{CE} = 5 V, I _C = 200 mA	60	_	320	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 500 mA, I _B = 50 mA	_	_	1.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 5 mA	0.5	_	0.8	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 200 mA	20	100	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	13	20	pF

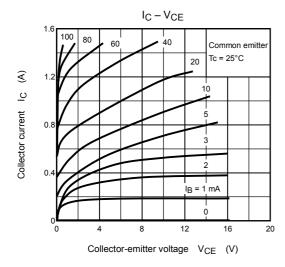
Note: $h_{\mbox{\scriptsize FE}}$ classification R: 60 to 120, O: 100 to 200, Y: 160 to 320

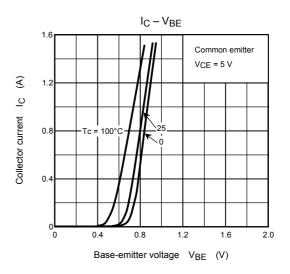
Marking

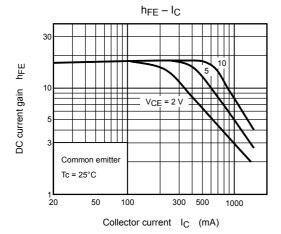


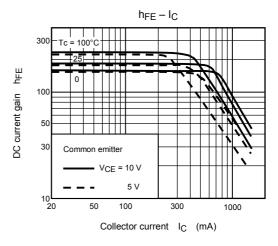
Explanation of Lot No.

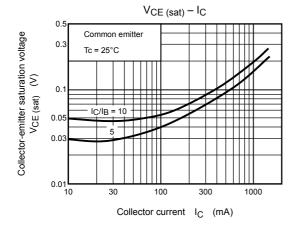


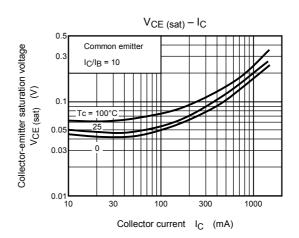




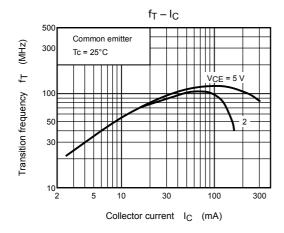


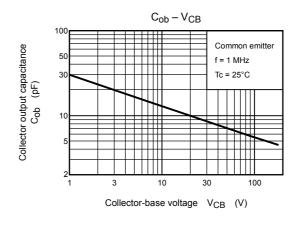


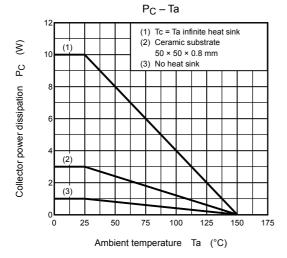


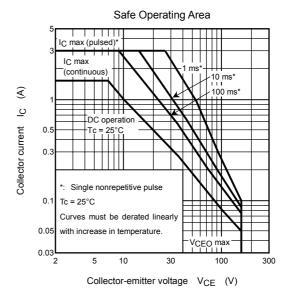


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